RoHS

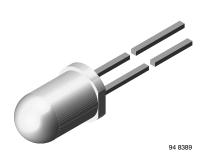
**GREEN** 

<u>(5-2008)</u>\*\*



# Vishay Semiconductors

# High Speed Infrared Emitting Diode, 890 nm, GaAlAs Double Hetero



## **DESCRIPTION**

TSHF6410 is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

#### **FEATURES**

Package type: leaded
Package form: T-1¾
Dimensions (in mm): Ø 5

Peak wavelength: λ<sub>p</sub> = 890 nm

High reliability

· High radiant power

High radiant intensity

Angle of half intensity: φ = ± 22°

· Low forward voltage

· Suitable for high pulse current operation

High modulation bandwidth: f<sub>c</sub> = 12 MHz

· Good spectral matching with Si photodetectors

 Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### Note

\*\* Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

#### **APPLICATIONS**

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK coded, 450 kHz or 1.3 MHz)

PRODUCT SUMMARY					
COMPONENT	I <sub>e</sub> (mW/sr)	φ (deg)	$\lambda_{\mathbf{P}}$ (nm)	tr (ns)	
TSHF6410	70	± 22	890	30	

#### Note

Test conditions see table "Basic Characteristics"

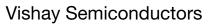
ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSHF6410	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾	

#### Note

MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		$V_{R}$	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1.5	А	
Power dissipation		P <sub>V</sub>	160	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R <sub>thJA</sub>	230	K/W	

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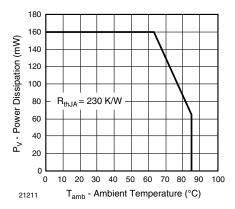


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

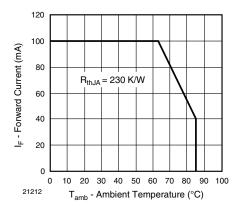


Fig. 1 - Forward Current Limit vs. Ambient Temperature

PARAMETER	CS (T <sub>amb</sub> = 25 °C, unless other TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>		1.4	1.6	V
	$I_F = 1 \text{ A, } t_D = 100  \mu\text{s}$	V <sub>F</sub>		2.3		V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>		- 1.8		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			10	μA
Junction capacitance	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	Cj		125		pF
Radiant intensity	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	I <sub>e</sub>	45	70	135	mW/sr
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	l <sub>e</sub>		700		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фe		50		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 100 mA	TKφ <sub>e</sub>		- 0.35		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	I <sub>F</sub> = 100 mA	λρ		890		nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		40		nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>		0.25		nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>		30		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		30		ns
Cut-off frequency	I <sub>DC</sub> = 70 mA, I <sub>AC</sub> = 30 mA pp	f <sub>c</sub>		12		MHz
Virtual source diameter		d		2.1		mm



# **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

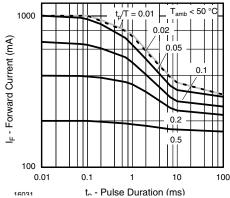


Fig. 2 - Pulse Forward Current vs. Pulse Duration

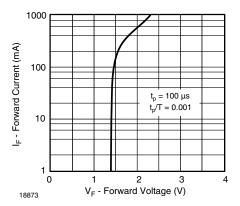


Fig. 3 - Forward Current vs. Forward Voltage

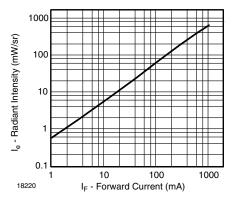


Fig. 4 - Radiant Intensity vs. Forward Current

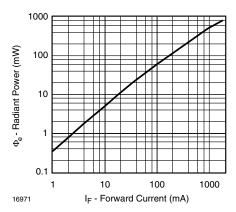


Fig. 5 - Radiant Power vs. Forward Current

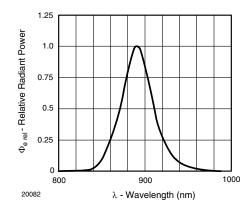


Fig. 6 - Relative Radiant Power vs. Wavelength

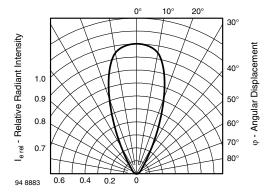
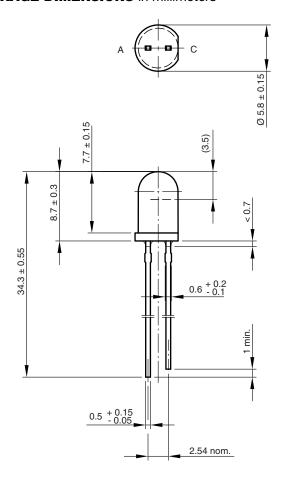
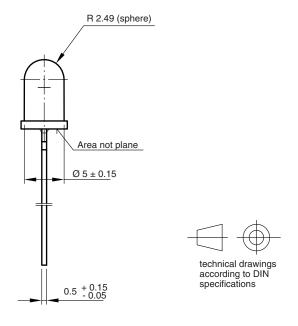


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

# Vishay Semiconductors

### **PACKAGE DIMENSIONS** in millimeters





Drawing-No.: 6.544-5259.06-4

Issue: 6; 19.05.09

19257

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